



ELECTRONICS, INC.

44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748-5089
<http://www.nteinc.com>

NTE6810 Integrated Circuit 128 x 8–Bit Static Random Access Memory (SRAM)

Description:

The NTE6810 is a byte–organized memory in a 24–Lead DIP type package designed for use in bus–organized systems. It is fabricated with N–channel silicon–gate technology. For ease of use, this device operates from a single power supply, has compatibility with TTL and DTL, and needs no clocks or refreshing because of static operation.

The memory is compatible with the 6800 Microcomputer Family, providing random storage in byte increments. Memory expansion is provided through multiple Chip Select inputs.

Features:

- Organized as 128 Bytes of 8–Bits
- Static Operation
- Bidirectional Three–State Data Input/Output
- Six Chip Select Inputs (Four Active Low, Two Active High)
- Single 5V Power Supply
- TTL Compatible
- Maximum Access Time: 450ns

Absolute Maximum Ratings:

| | |
|--|----------------|
| Supply Voltage, V_{CC} | –0.3 to +7V |
| Input Voltage, V_{in} | –0.3 to +7V |
| Operating Temperature Range, T_A | 0° to +70°C |
| Storage Temperature Range, T_{stg} | –65° to +150°C |
| Thermal Resistance, Junction to Ambient, $R_{\theta JA}$ | +120°C/W |

Note 1. This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage (e.g., either V_{SS} or V_{CC}).

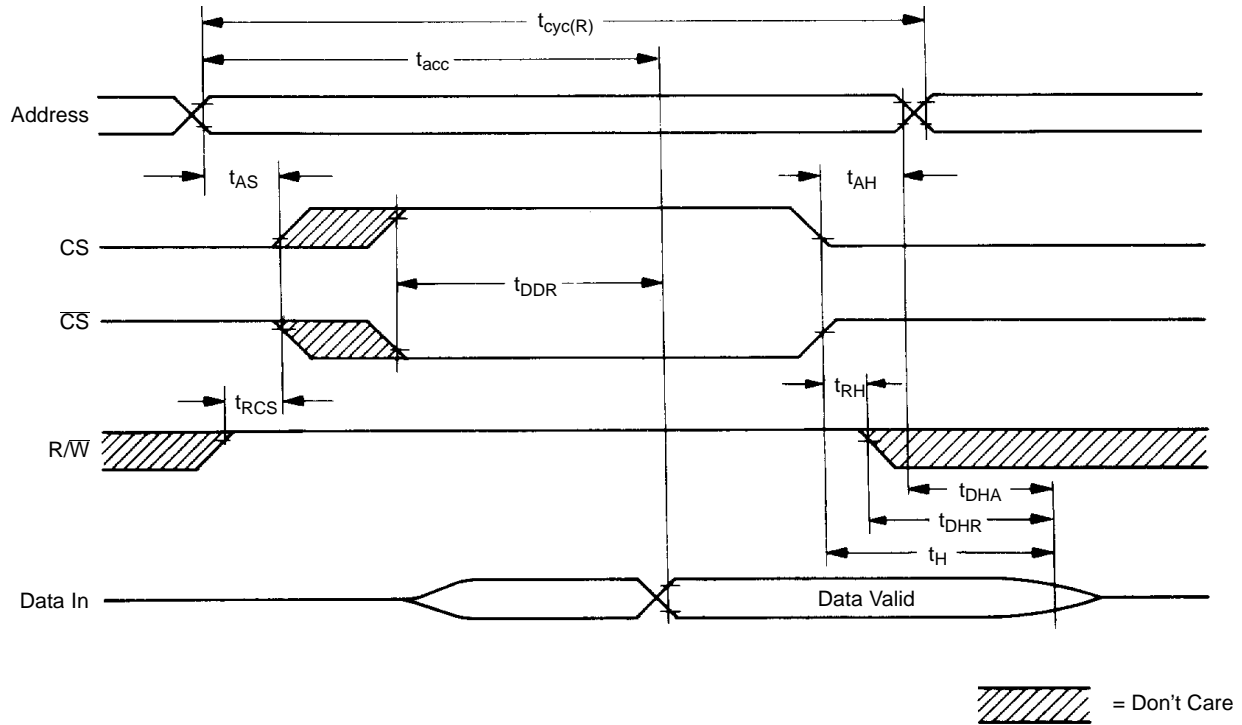
DC Electrical Characteristics: ($V_{CC} = 5V \pm 5\%$, $V_{SS} = 0$, $T_A = 0^\circ$ to $+70^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Max | Unit |
|--|-----------|---|----------------|----------------|---------------|
| Input High Voltage | V_{IH} | | $V_{SS} + 2.0$ | V_{CC} | V |
| Input Low Voltage | V_{IL} | | $V_{SS} - 0.3$ | $V_{SS} + 0.8$ | V |
| Input Current (A_n , R/\overline{W} , \overline{CS}_n) | I_{in} | $V_{in} = 0$ to $5.25V$ | – | 2.5 | μA |
| Output High Voltage | V_{OH} | $I_{OH} = -205\mu\text{A}$ | 2.4 | – | V |
| Output Low Voltage | V_{OL} | $I_{OL} = 1.6\text{mA}$ | – | 0.4 | V |
| Output Leakage Current (Three-State) | I_{TSI} | $CS = 0.8V$ or $\overline{CS} = 2V$, $V_{out} = 0.4V$ to $2.4V$ | – | 10 | μA |
| Supply Current | I_{CC} | $V_{CC} = 5.25V$, All other pins grounded | – | 80 | mA |
| Input Capacitance (A_n , R/\overline{W} , CS_n , \overline{CS}_n) | C_{in} | $V_{in} = 0$, $T_A = +25^\circ\text{C}$, $f = 1\text{MHz}$ | – | 7.5 | pF |
| Output Capacitance (D_n) | C_{out} | $V_{out} = 0$, $T_A = +25^\circ\text{C}$, $f = 1\text{MHz}$, $CSO = 0$ | – | 12.5 | pF |

AC Operating Conditions and Characteristics:

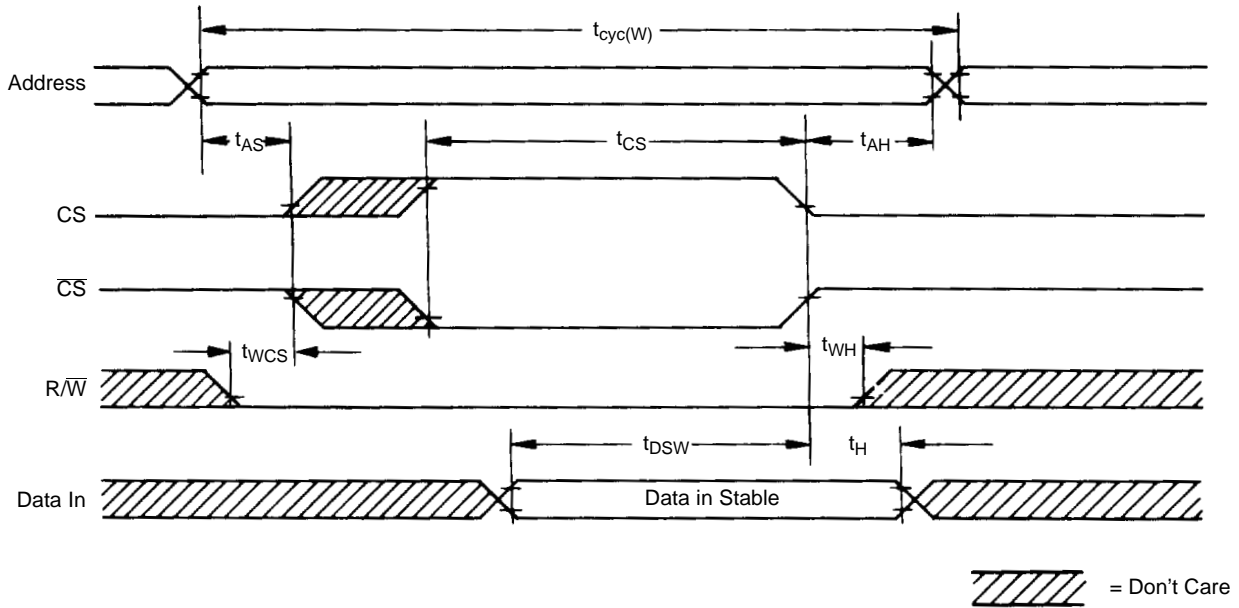
| Parameter | Symbol | Min | Max | Unit |
|--|--------------|-----|-----|------|
| Read Cycle ($V_{CC} = 5V \pm 5\%$, $V_{SS} = 0$, $T_A = 0^\circ$ to $+70^\circ$ unless otherwise specified) | | | | |
| Read Cycle Time | $t_{cyc(R)}$ | 450 | – | ns |
| Access Time | t_{acc} | – | 450 | ns |
| Address Setup Time | t_{AS} | 20 | – | ns |
| Address Hold Time | t_{AH} | 0 | – | ns |
| Data Delay Time (Read) | t_{DDR} | – | 230 | ns |
| Read to Select Delay Time | t_{RCS} | 0 | – | ns |
| Data Hold from Address | t_{DHA} | 10 | – | ns |
| Output Hold Time | t_H | 10 | – | ns |
| Data Hold from Read | t_{DHR} | 10 | 80 | ns |
| Read Hold from Chip Select | t_{RH} | 0 | – | ns |
| Write Cycle ($V_{CC} = 5V \pm 5\%$, $V_{SS} = 0$, $T_A = 0^\circ$ to $+70^\circ$ unless otherwise specified) | | | | |
| Write Cycle Time | $t_{cyc(W)}$ | 450 | – | ns |
| Address Setup Time | t_{AS} | 20 | – | ns |
| Address Hold Time | t_{AH} | 0 | – | ns |
| Chip Select Pulse Width | t_{CS} | 300 | – | ns |
| Write to Chip Select Delay Time | t_{WCS} | 0 | – | ns |
| Data Setup Time (Write) | t_{DSW} | 190 | – | ns |
| Input Hold Time | t_H | 10 | – | ns |
| Write Hold Time from Chip Select | t_{WH} | 0 | – | ns |

Read Cycle Timing



- Note 1. Voltage levels shown are $V_L \leq 0.4V$, $V_H \geq 2.4V$, unless otherwise specified.
 Note 2. Measurement points as shown are 0.8V and 2.0V, unless otherwise specified.
 Note 3. CS and \overline{CS} have same timing.

Write Cycle Timing



- Note 1. Voltage levels shown are $V_L \leq 0.4V$, $V_H \geq 2.4V$, unless otherwise specified.
 Note 2. Measurement points as shown are 0.8V and 2.0V, unless otherwise specified.
 Note 3. CS and \overline{CS} have same timing.

Pin Connection Diagram

